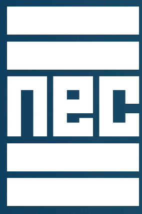
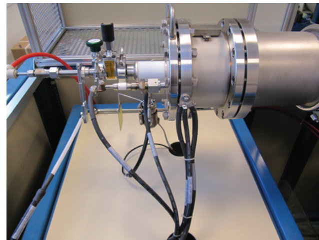


How Science BREAKS THROUGH

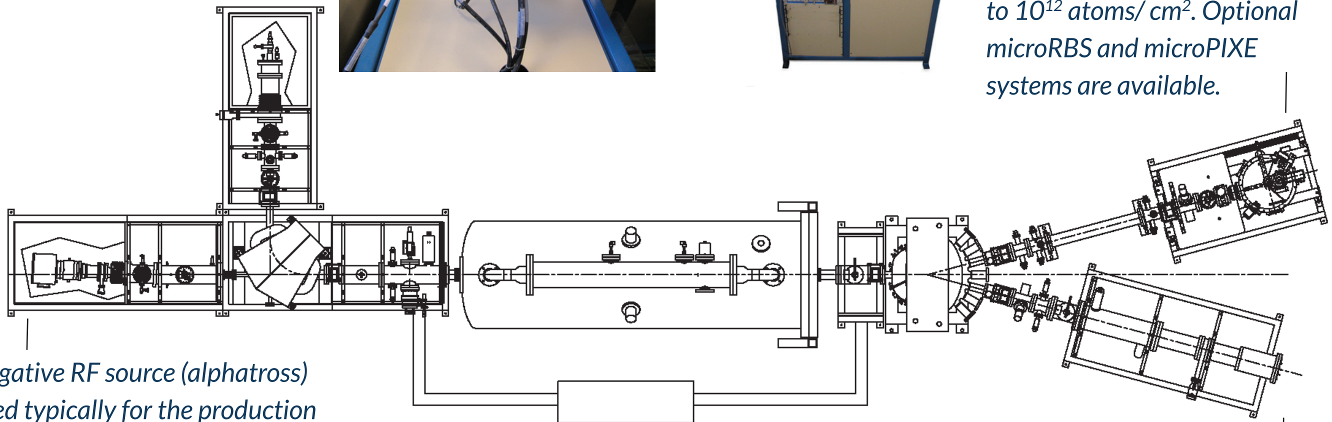
NEC offers research grade implantation and Ion Beam Analysis chambers in one system

– systems can include heavy ion sources for implantation and light ion sources for IBA

SNICS ion source capable of producing all negative ions across the periodic table except noble gases

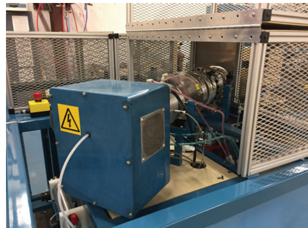


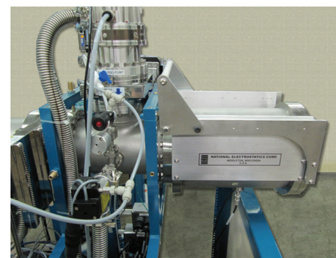
Analysis endstation that can include detector for RBS, Channeling, ERD, PIXE, PIGE, NRA, and IBIL. Offers monolayer depth resolution and sensitivity to 10^{12} atoms/ cm^2. Optional microRBS and microPIXE systems are available.



1 MV Pelletron for IBA and implantation

Negative RF source (alphatross) used typically for the production of hydrogen and helium, though can also produce beams from other gases such as oxygen and nitrogen





Single and multi-wafer implant chambers are available as well as custom chambers based on user specifications. Typical implantation range from 10^{12} to 10^{17} atoms /cm^2

How are samples affected or changed when interacting with ion beams? To find out, NEC offers:

- Open Air ion implantation systems for beam energies in the 50 to 500 keV range.
- Single-ended or tandem accelerators for beam energies from 10's of keV to 10's of MeV.
- High temperature (800° C) and low temperature implant chambers.

Contact NEC

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